

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

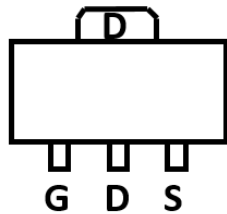
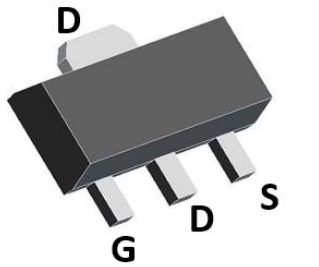
• V_{DS}	60V
• I_D	3.0A
• $R_{DS(ON)}$ (at $V_{GS}=10V$)	<100 mohm
• $R_{DS(ON)}$ (at $V_{GS}=4.5V$)	<120 mohm

General Description

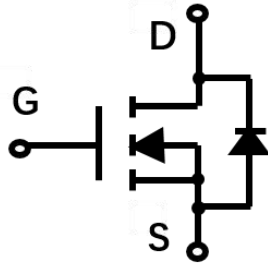
- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

- DC-DC Converters
- Power management functions



SOT-89



■ Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	60	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25^{\circ}\text{C}$	I_D	3	A
	$T_A=70^{\circ}\text{C}$		2.4	
Pulsed Drain Current ^A		I_{DM}	12	A
Total Power Dissipation @ $T_c=25^{\circ}\text{C}$		P_D	0.69	W
Thermal Resistance Junction-to-Ambient ^B		$R_{\theta JA}$	181	$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^{\circ}\text{C}$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJH03N06A	F1		1000	10000	40000	7" reel



YJH03N06A

■ Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS1}	V _{GS} = ±20V, V _{DS} =0V			±100	nA
	I _{GSS2}	V _{GS} = ±10V, V _{DS} =0V			±50	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	1.0	1.3	2.0	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D =3A		86	100	mΩ
		V _{GS} = 4.5V, I _D =2A		92	120	
Diode Forward Voltage	V _{SD}	I _S =3.0A,V _{GS} =0V		0.8	1.2	V
Maximum Body-Diode Continuous Current	I _S				3.0	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =30V,V _{GS} =0V,f=1MHZ		330		pF
Output Capacitance	C _{oss}			90		
Reverse Transfer Capacitance	C _{rss}			17		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V,V _{DS} =30V,I _D =3.0A		5.1		nC
Gate-Source Charge	Q _{gs}			1.3		
Gate-Drain Charge	Q _{gd}			1.7		
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V,V _{DD} =30V, I _D =1.5A,R _L =1Ω R _{GEN} =3Ω		13		ns
Turn-on Rise Time	t _r			51		
Turn-off Delay Time	t _{D(off)}			19		
Turn-off fall Time	t _f			12		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.



■ Typical Performance Characteristics

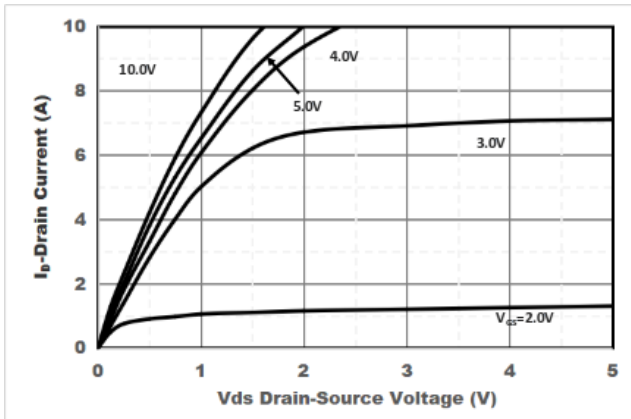


Figure1. Output Characteristics

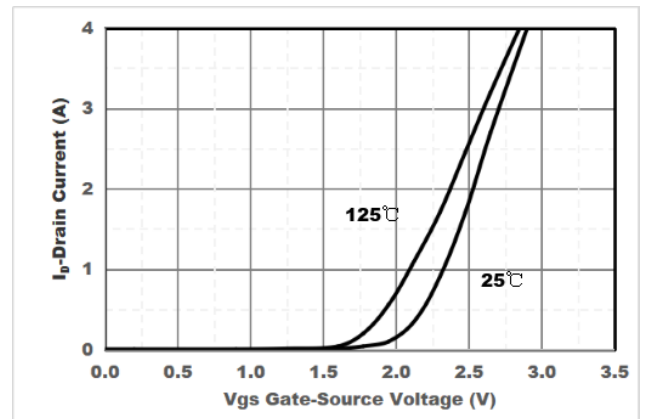


Figure2. Transfer Characteristics

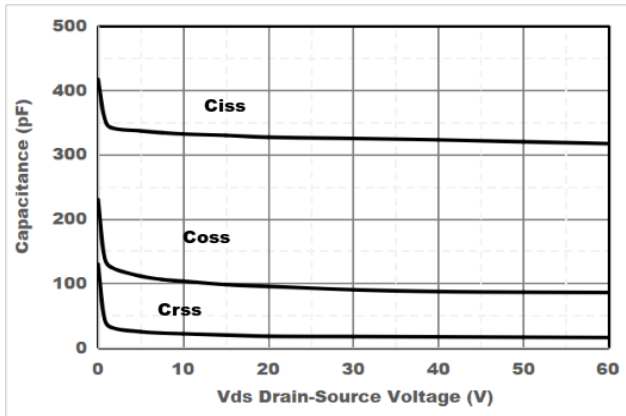


Figure3. Capacitance Characteristics

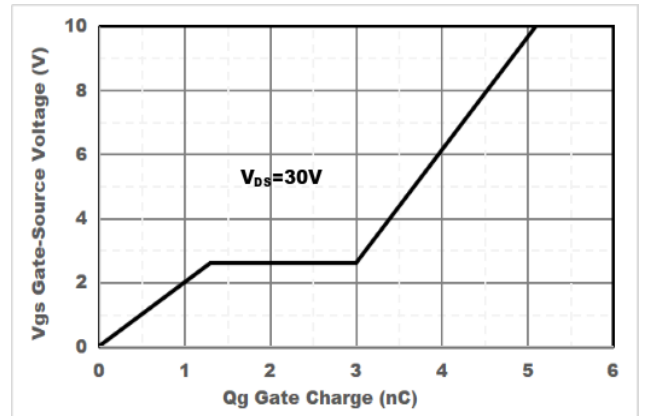


Figure4. Gate Charge

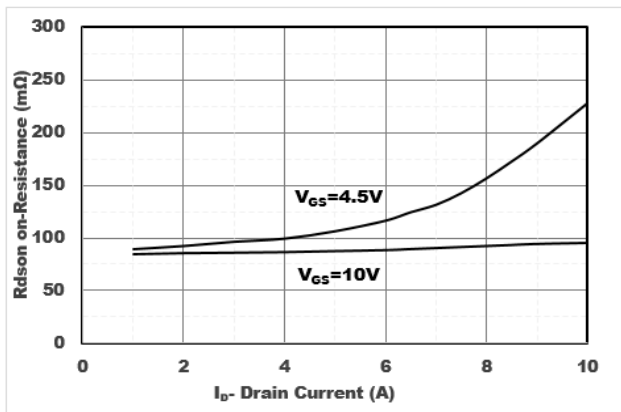


Figure5. Drain-Source on Resistance

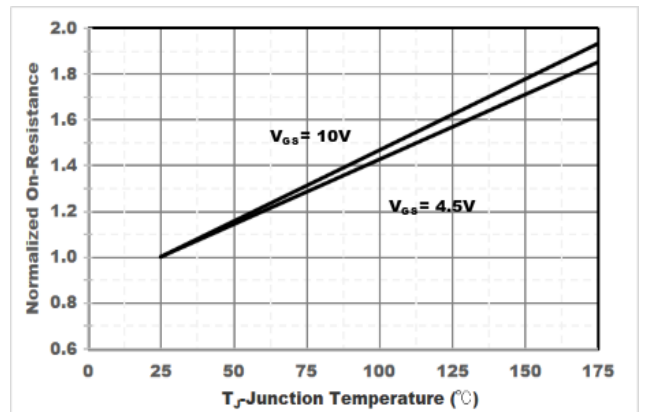


Figure6. Drain-Source on Resistance

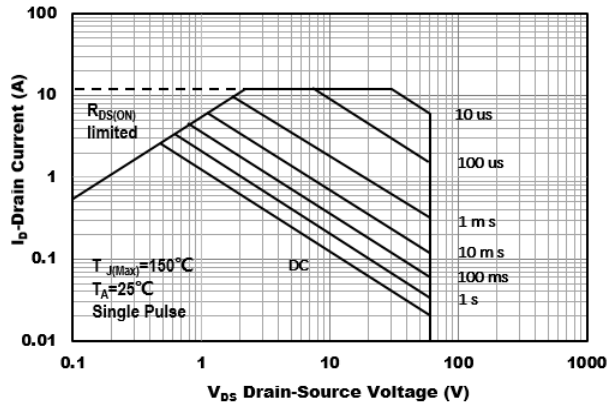


Figure7. Safe Operation Area

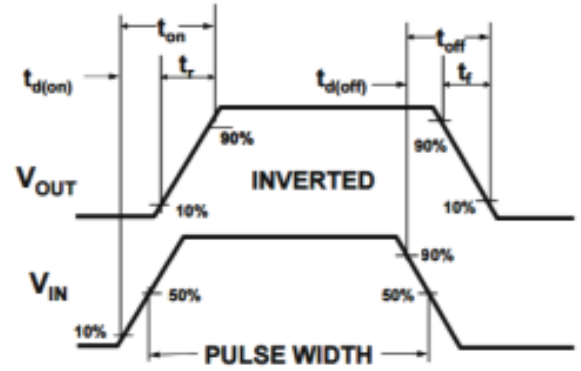
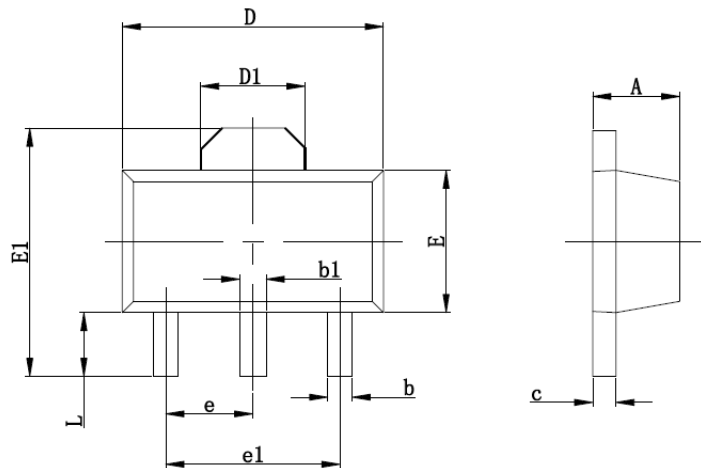


Figure8. Switching wave



■ SOT-89 Package information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.350	0.520	0.013	0.197
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF		0.061 REF	
E	2.350	2.550	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP		0.060TYP	
e1	3.000 TYP		0.118TYP	
L	0.900	1.100	0.035	0.047



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